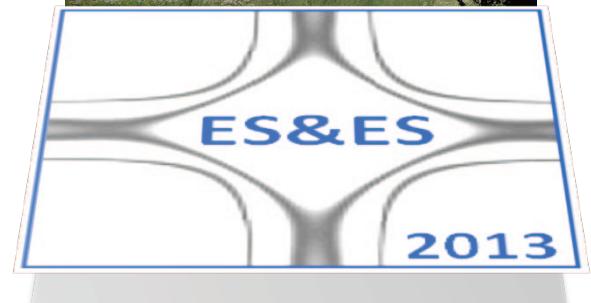


ARPES investigations of bulk insulating topological insulators

Mark S. Golden
Van der Waals-Zeeman Institute
IoP
University of Amsterdam



Thanks to



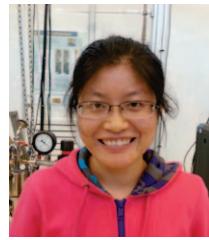
Yingkai
Huang



Dong
Wu



Anne de
Visser



Yu Pan



Huib
Luigjes



Bay
Tran



Shira
Hollanders



Takashi
Nakai



Erik van
Heumen



Emmanouil
Frantzeskakis



Nick de
Jong



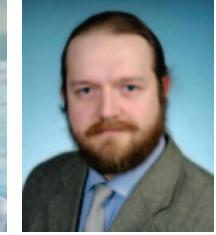
Berend
Zwartenberg



Erik
Slooten



Ming Shi



Andrei
Varykhakov

+ Emile
Rienks



Jeroen
Goedkoop



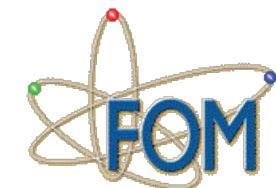
Jochem
Kaas



Jiri
Oen



Steve
Johnston



What's special about topological insulators ?

Highly original & deep insights from
theoretical physics



Difficult, yet possible experimental challenges:
'doable' on a 5-10(+) year scale



New 'elementary' particle, new superconductors
fault tolerant quantum computation



NATURE | NEWS

Google and NASA snap up quantum computer

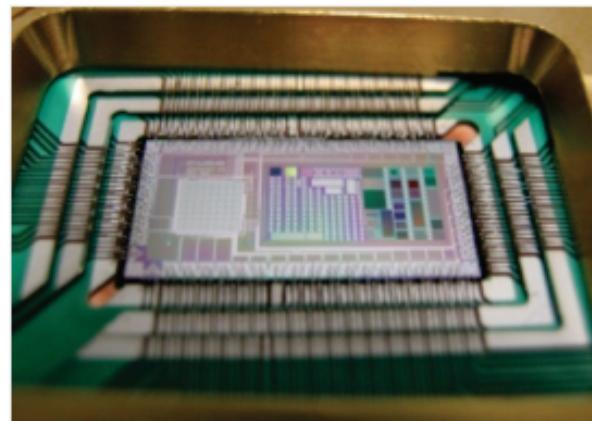
D-Wave machine to work on artificial-intelligence problems.

Nicola Jones

16 May 2013

D-Wave, the small company that sells the world's only commercial quantum computer, has just bagged an impressive new customer: a collaboration between Google, NASA and the non-profit Universities Space Research Association.

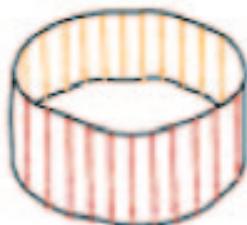
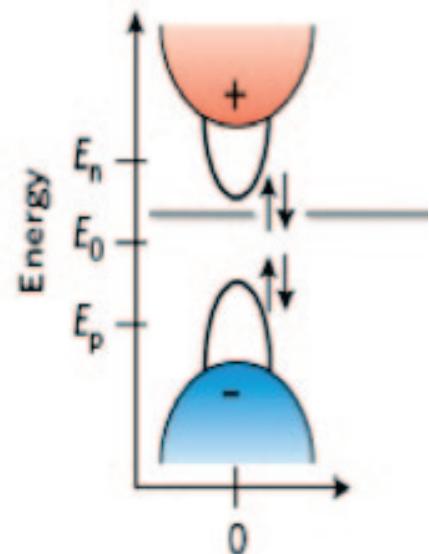
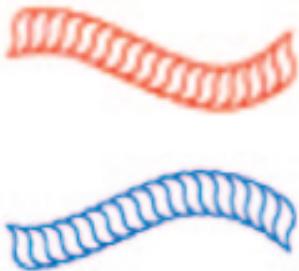
The three organizations have joined forces to install a D-Wave Two, the computer company's latest model, in a facility launched by the collaboration — the Quantum Artificial Intelligence Lab at NASA's Ames Research Center in Moffett Field, California. The lab will explore areas such as machine learning —



The D-Wave Two quantum computer has a 512-qubit processor (pictured) that can do some calculations thousands of times faster than conventional computers.

D-WAVE

Surface states



regular band structure:
no twist

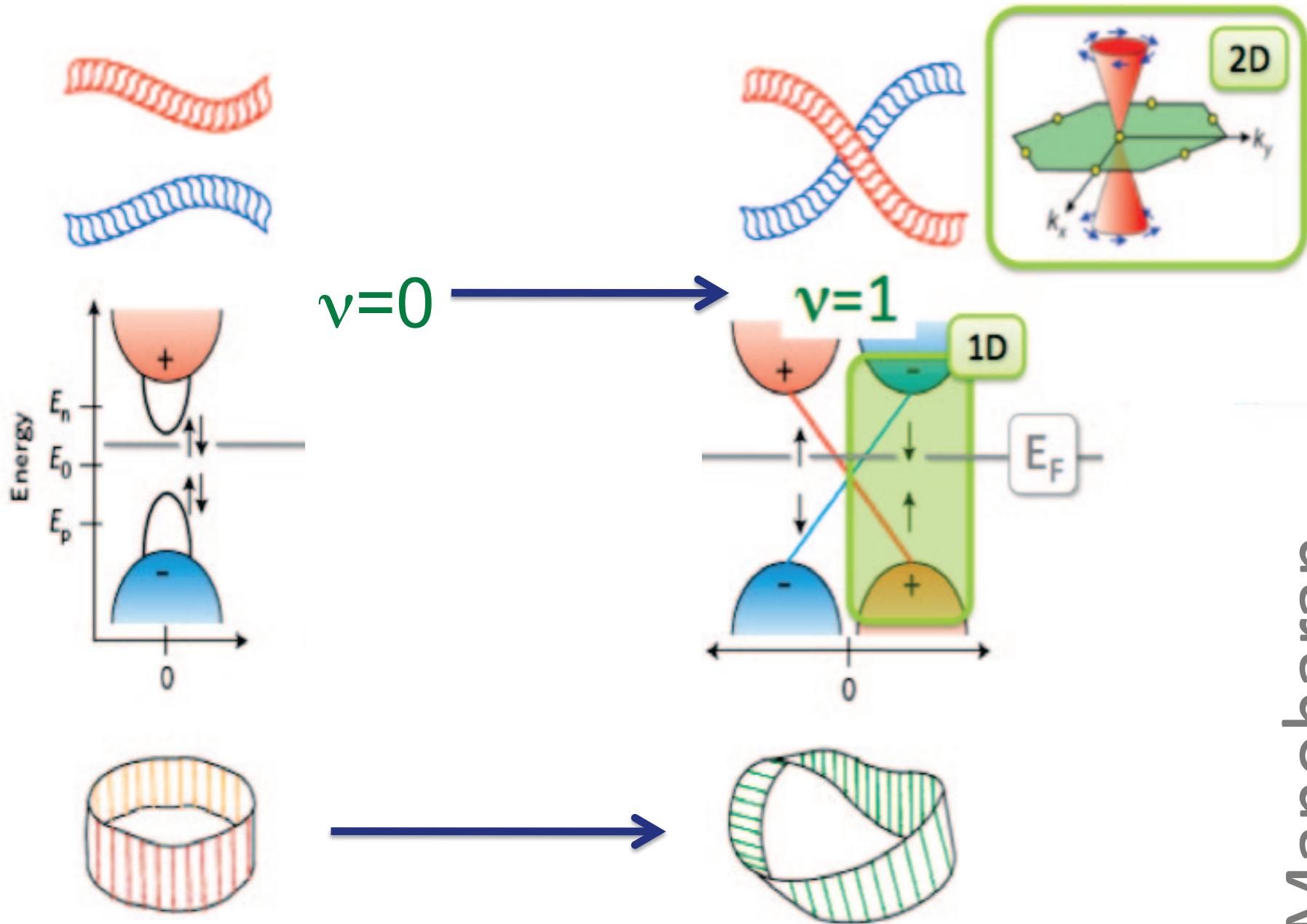


surface states in gap:
spin degenerate



they can cross E_F , but
can be gapped

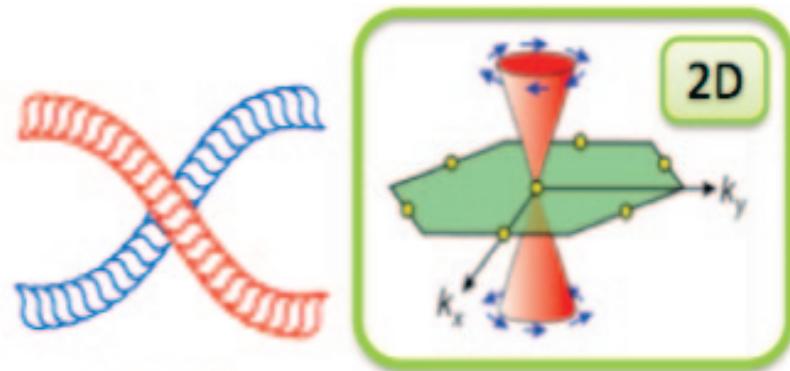
Add a twist to the band structure



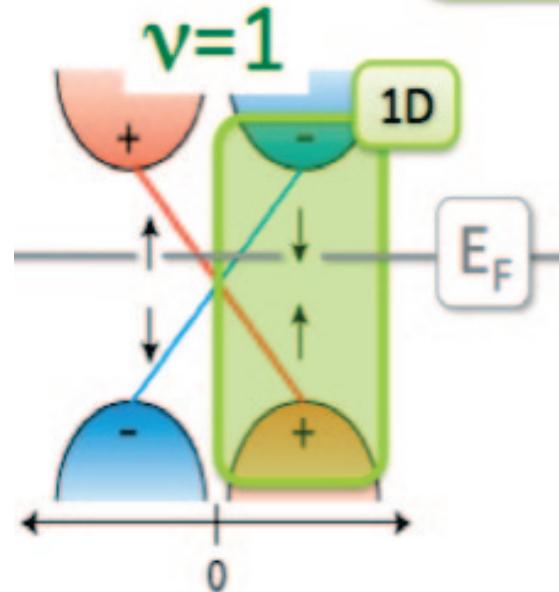
Manoharan

Edge states in topological insulators

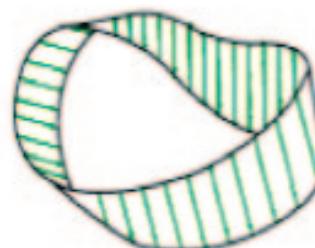
- e.g. 2D surface of 3D TI



- live in the gap:
100% spin polarized



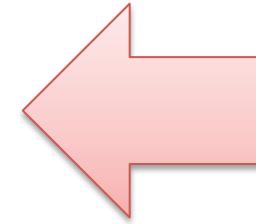
- they can't cross E_F
topological
protection



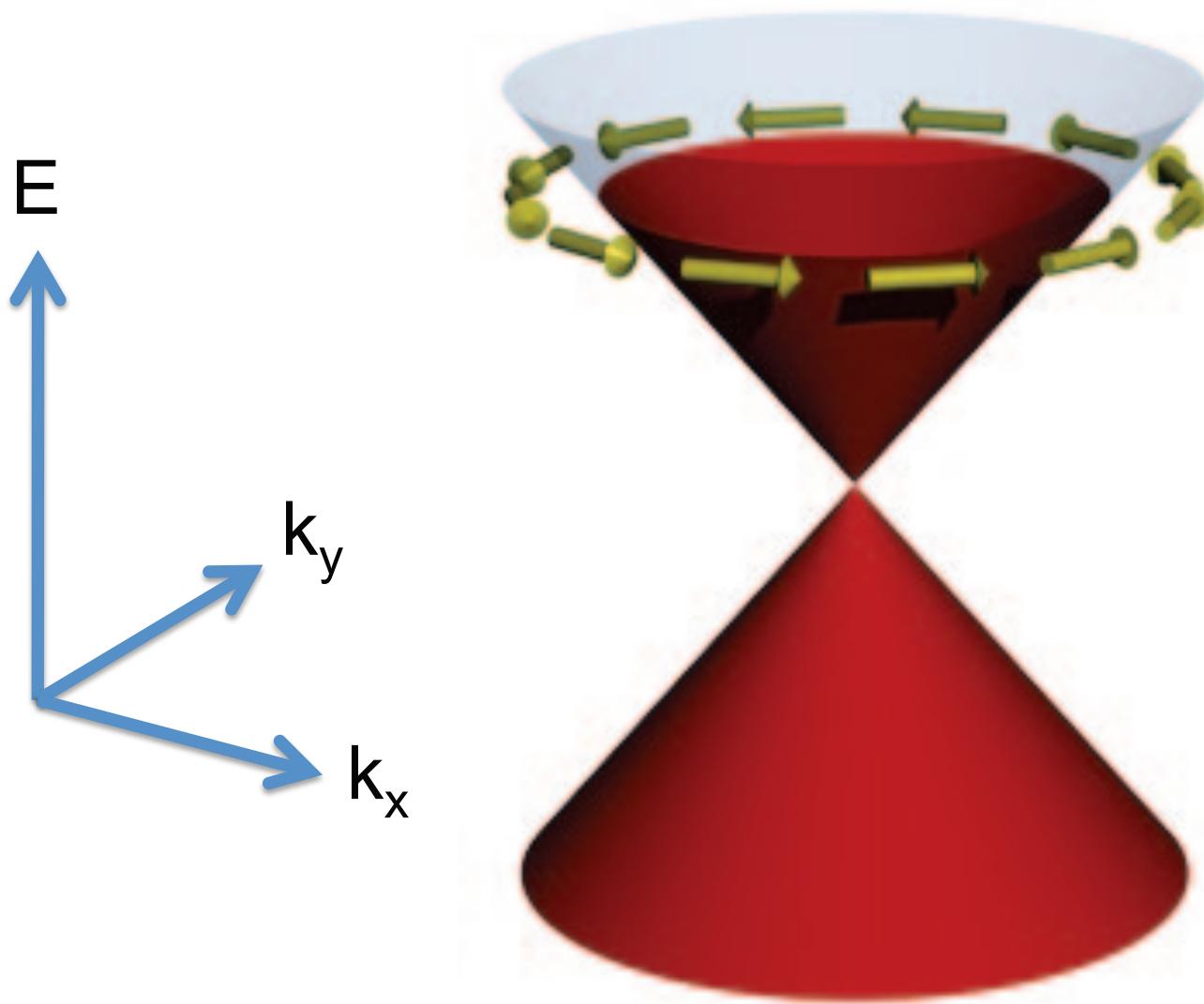
Manoharan

Overview

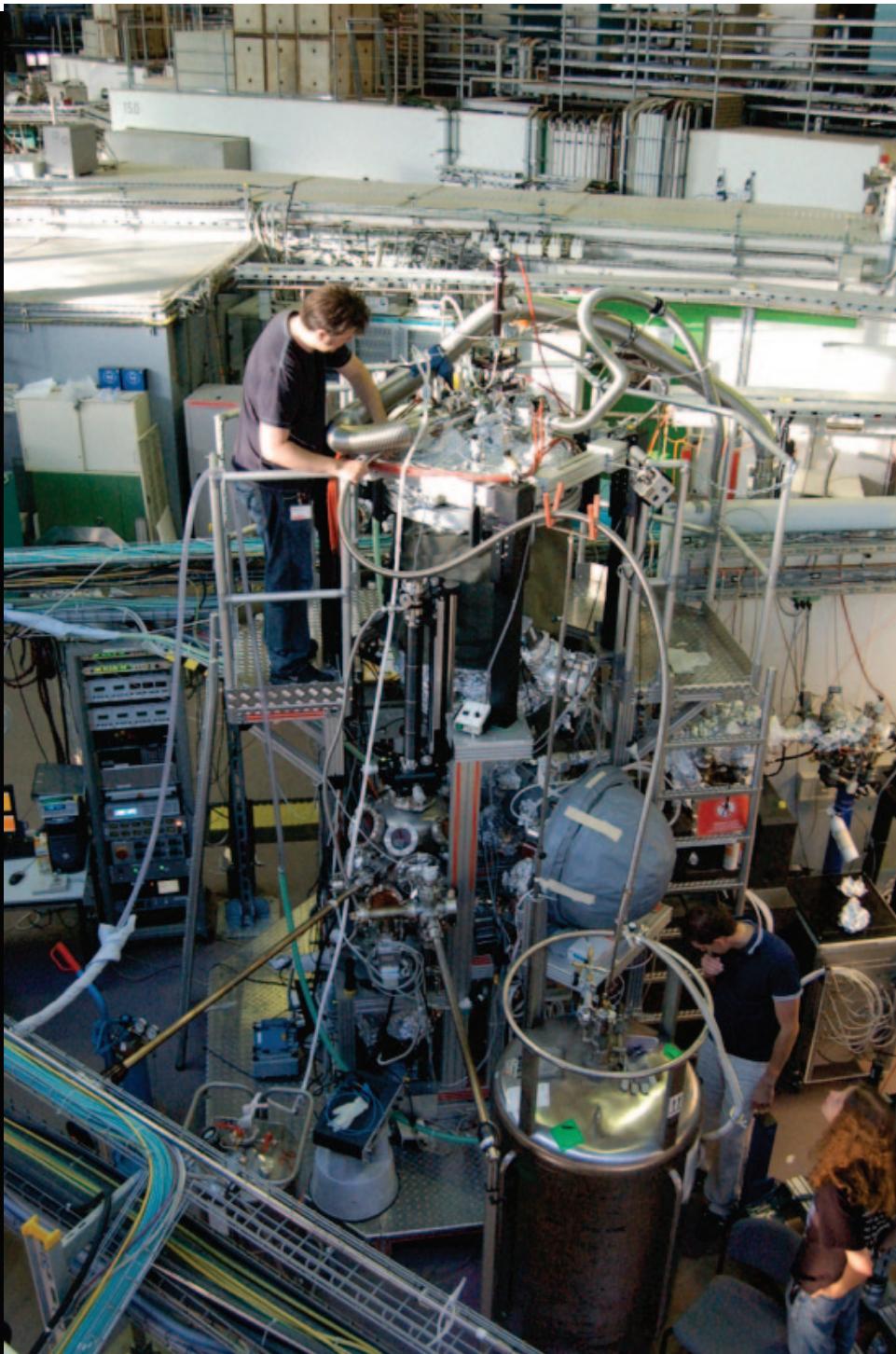
- hitchhiker's guide to TIs
- spectroscopy and microscopy of topological surface states
- towards 3D topological *insulators*



Dirac fermions with helical spin structure



Pic: Marcel Franz (UBC)



ARPES: gives birth to the 3D TI field

nature

LETTERS

Experimental Realization of a Three-Dimensional Topological Insulator, Bi_2Te_3

July 2009



A LETTERS JOURNAL EXPLORING THE FRONTIERS OF PHYSICS

D EPL, 81 (2008) 57006
doi: 10.1209/0295-5075/81/57006

March 2008

www.epljournal.org

O Q Spin-orbit interaction effect in the electronic structure of Bi_2Te_3 T observed by angle-resolved photoemission spectroscopy

D. I H.-J. NOH^{1,2(a)}, H. KOH², S.-J. OH², J.-H. PARK³, H.-D. KIM⁴, J. D. RAMEAU^{5,6}, T. VALLA⁵, T. E. KIDD⁵,
G. I P. D. JOHNSON⁵, Y. HU⁵ and Q. LI⁵

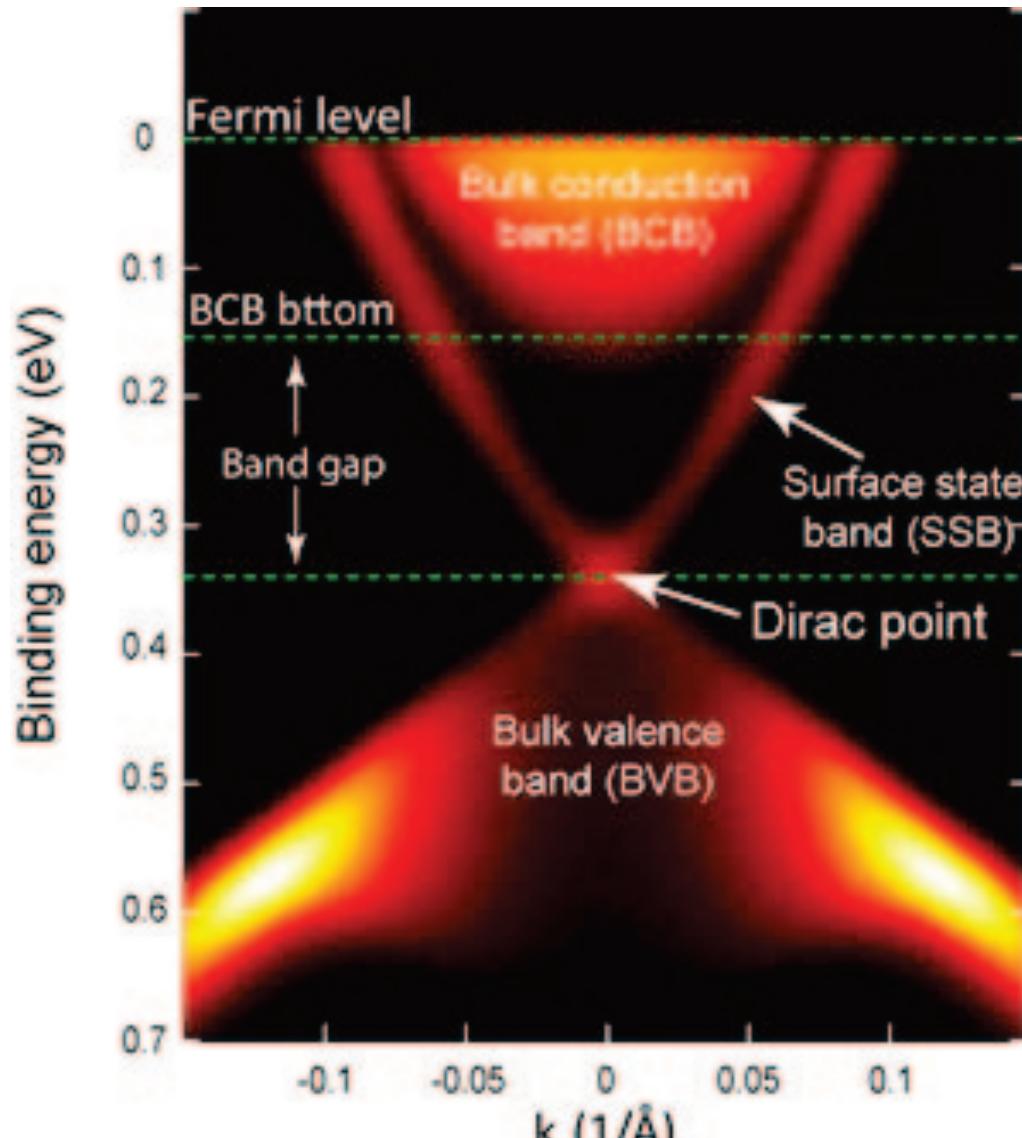
A topologically ordered state that evades the constraints of conventional matter. Exotic spin-orbit effects have been speculated in various spin-sensitive measurements, such as magnetooptical polarimetry, we probe the electronic properties of the topological insulator class with a single Dirac cone on the surface. These results are collectively carried out by the ARPES group at the University of California, Berkeley.

Observation of a large-gap topological-insulator class with a single Dirac cone on the surface

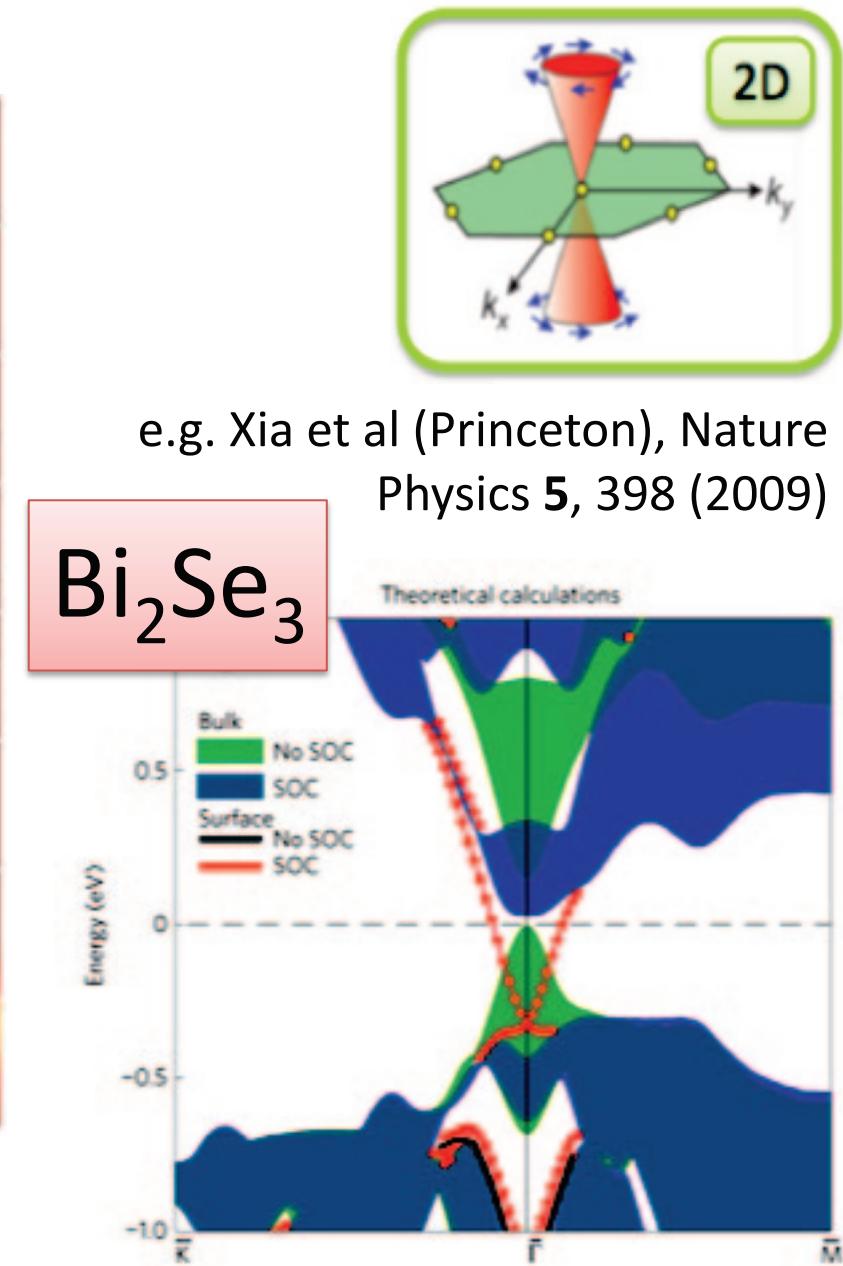
Y. XIA^{1,2}, D. QIAN^{1,3}, D. HSIEH^{1,2}, L. WRAY¹, A. PAL¹, H. LIN⁴, A. BANSIL⁴, D. GRAUER⁵, Y. S. HOR⁵, R. J. CAVA⁵ and M. Z. HASAN^{1,2,6*}

Feb 2009

Dirac cones in experiment (in odd number quantities)



Pic: Shen group, Stanford



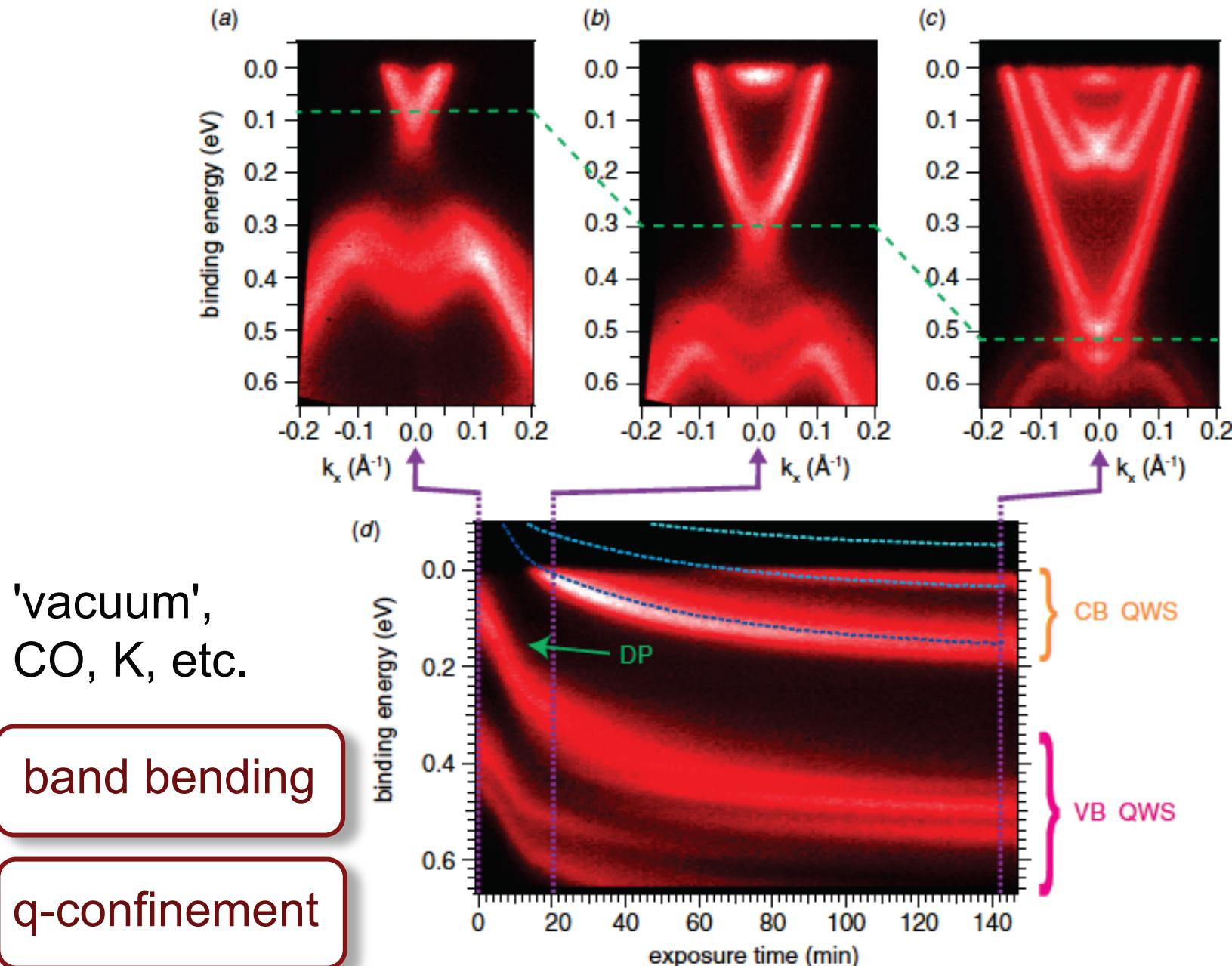
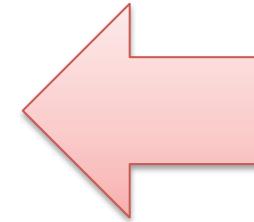


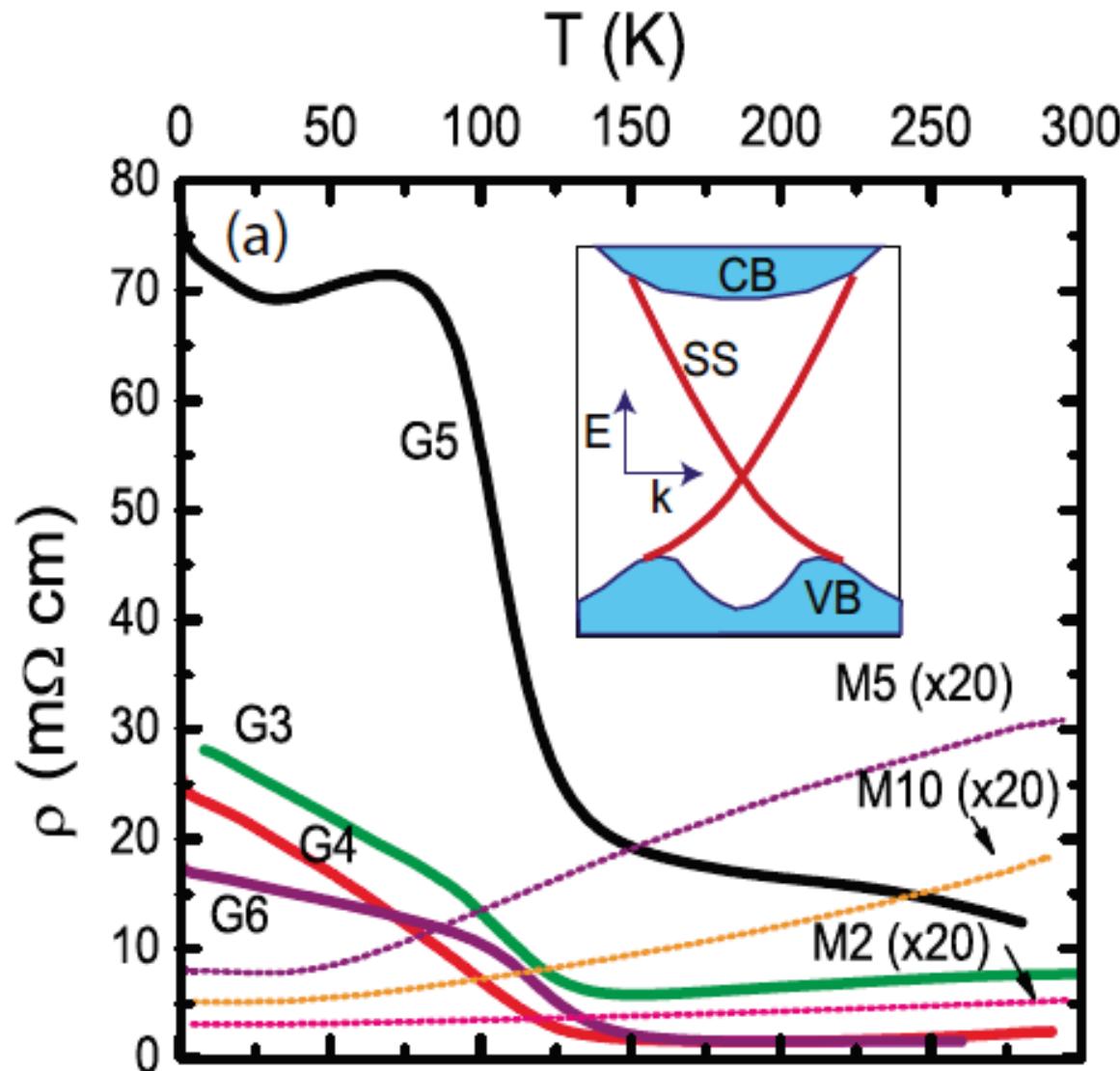
Figure 8. ARPES spectra acquired during the controlled dose of CO on Ca-doped Bi_2Se_3 ($h\nu = 16$ eV). The acquisition and dosing was

Overview

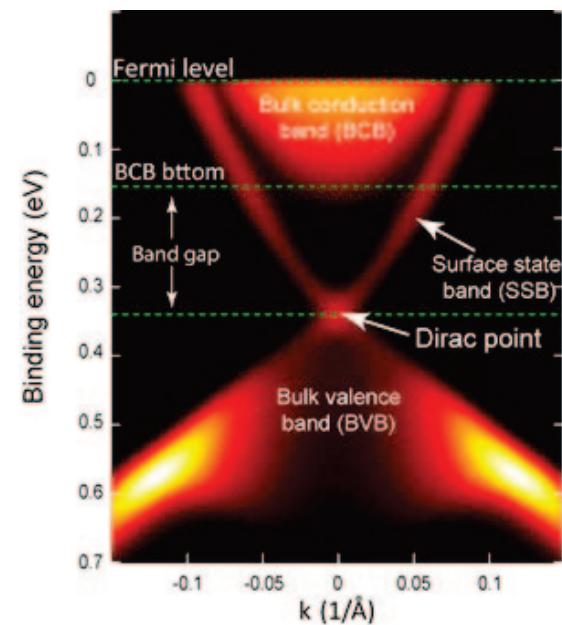
- hitchhiker's guide to TIs
- spectroscopy and microscopy of topological surface states
- towards 3D topological *insulators*



Bi_2Se_3 : bulk is not very insulating

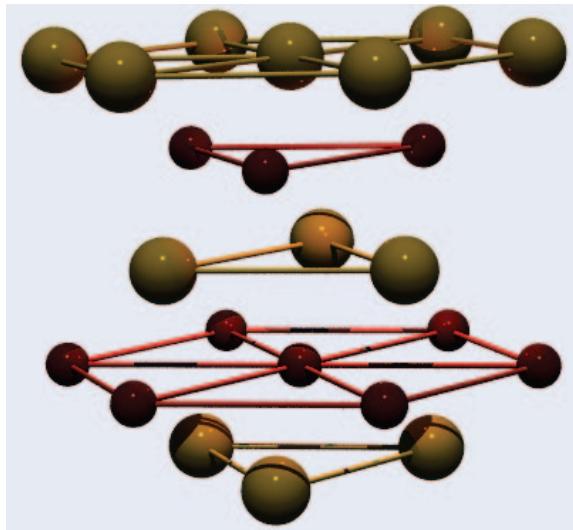


Se vacancies
in Bi_2Te_3 : also Bi – Te antisite defects

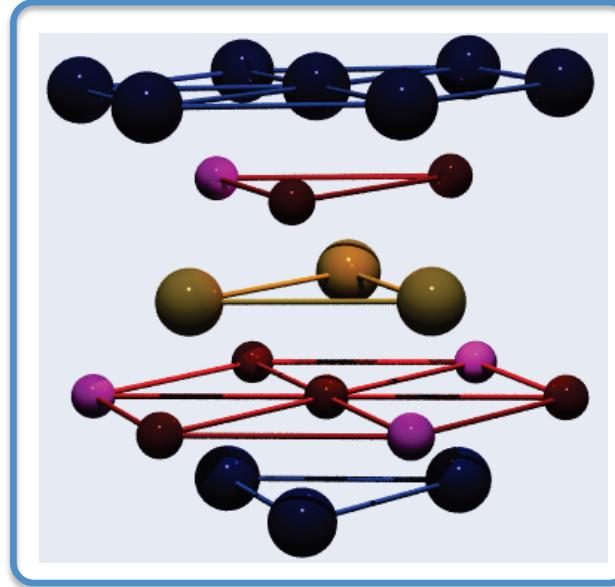


Ternary 3D TI's: e.g. $\text{Bi}_2\text{Te}_2\text{Se}$ and beyond

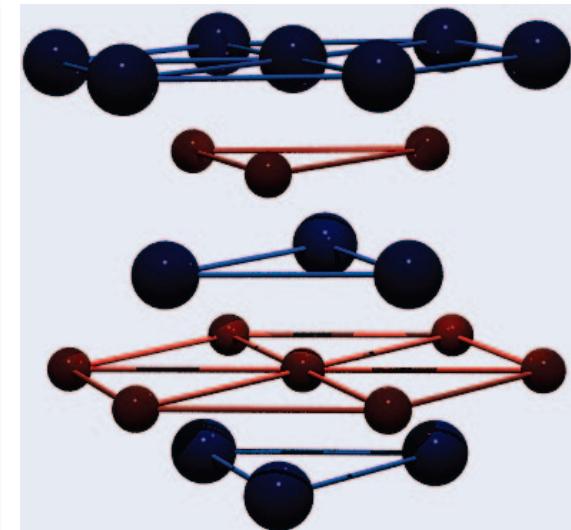
Bi_2Se_3



$\text{Bi}_x\text{Sb}_{2-x}\text{Te}_{3-y}\text{Se}_y$



Bi_2Te_3



Se stuck (strongly) between two Bi planes (less Se vacancies)



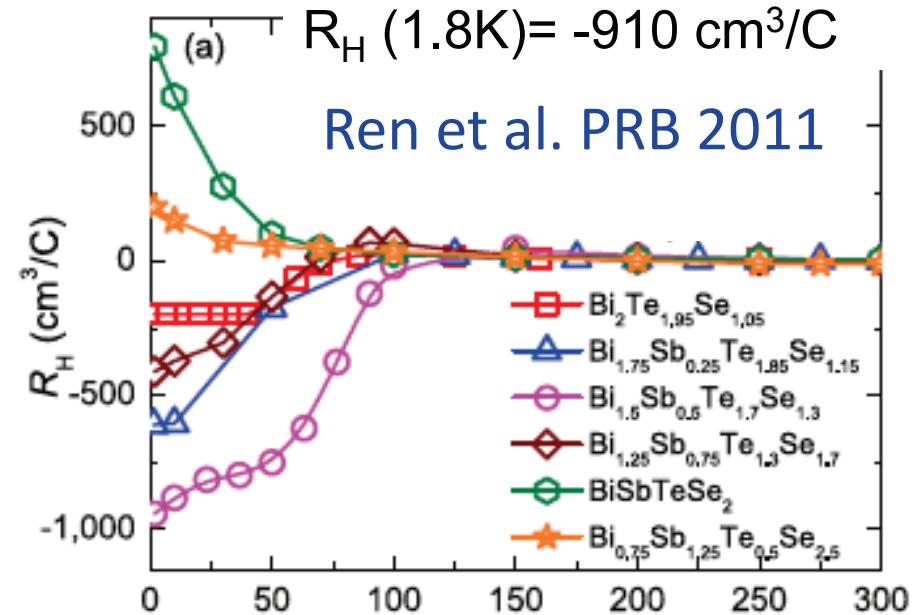
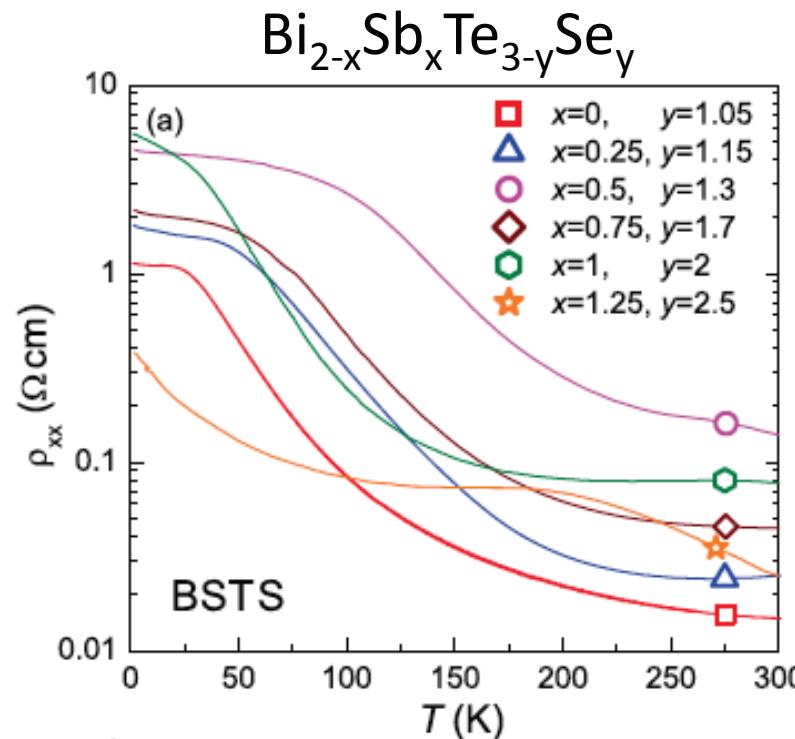
strong Bi-Se bonding (less Bi-Te antisite defects)

Y. Ando group, Cava group

Yingkai Huang, Dong Wu



Ando group: quaternaries – Bi-Sb-Te-Se = BSTS



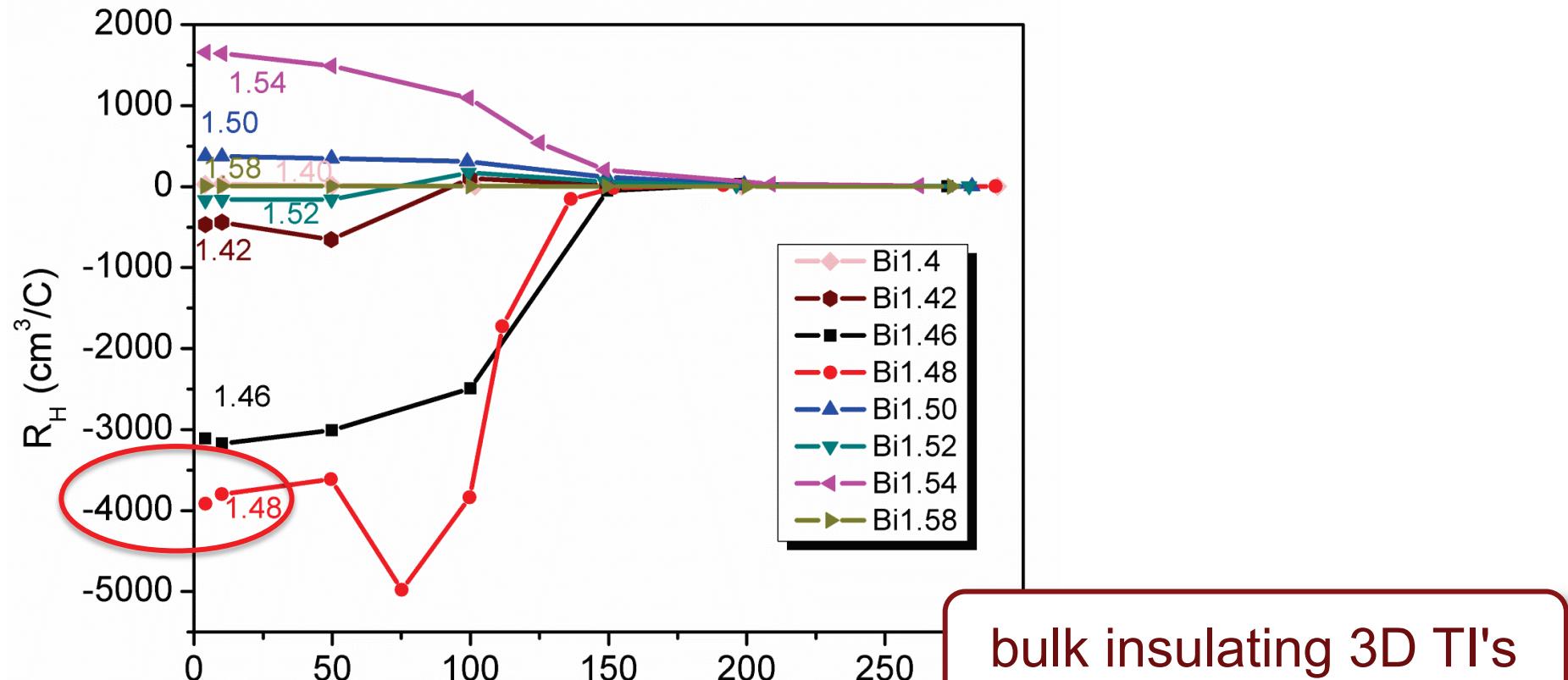
significant improvements cf. Bi_2Se_3 and doped Bi_2Se_3

resistivities close to 10 Ωcm

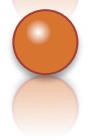
low T Hall coefficient: -910 cm^3/C

also Cava group

$\text{Bi}_x\text{Sb}_{2-x}\text{Te}_{1.7}\text{Se}_{1.3}$ – resistivity and Hall coefficient



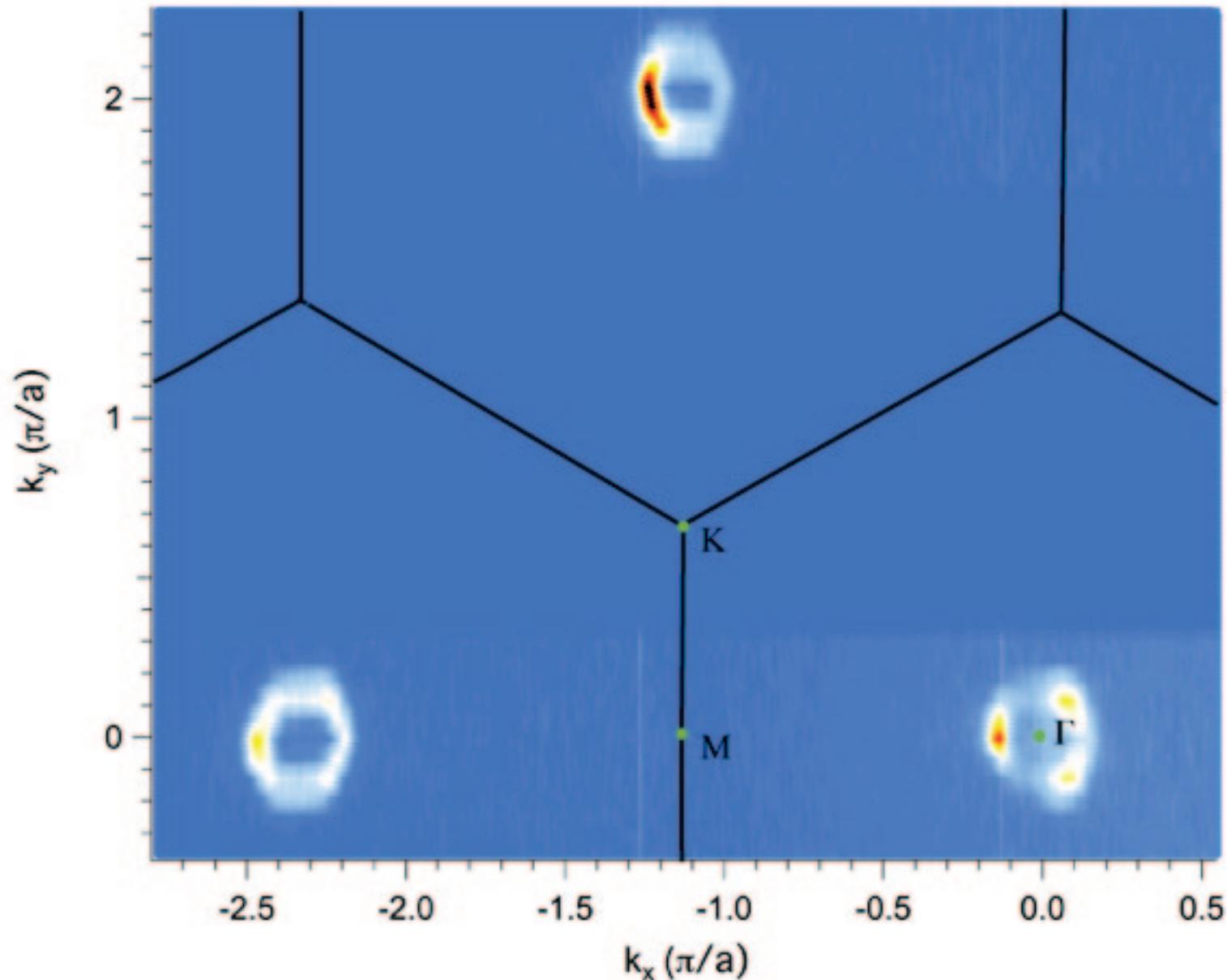
larger R_H than Osaka group (Ren, PRB 2011)



higher surface conductance and lower bulk conductivity
than Xia et al., PRB 2013 [Singapore]

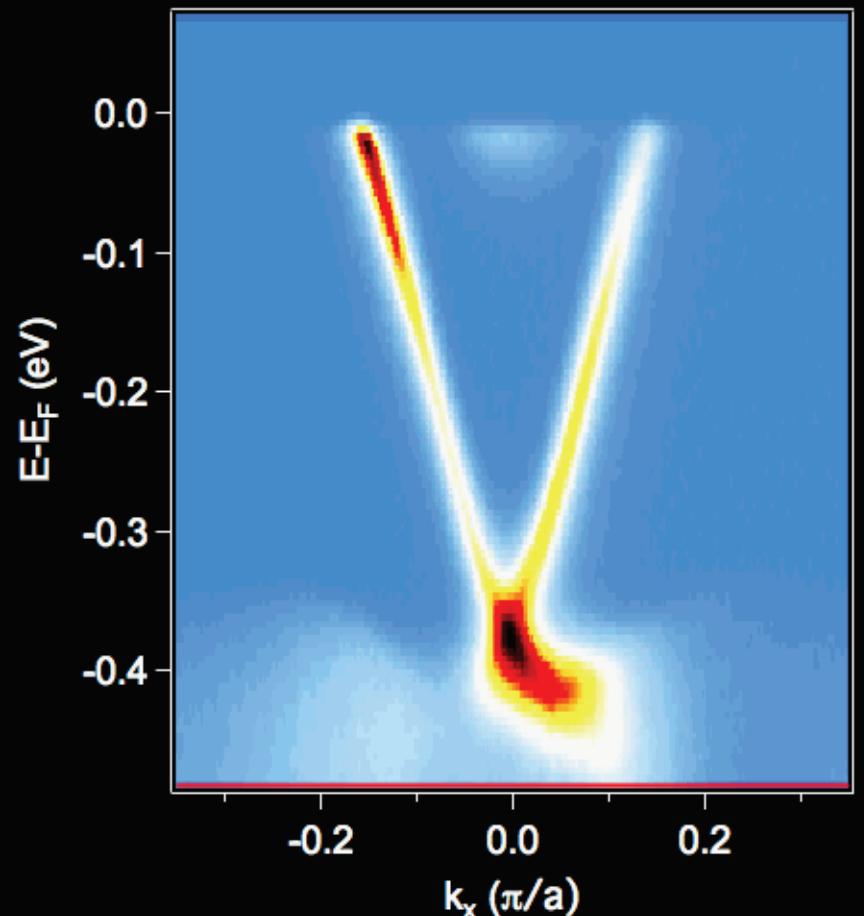
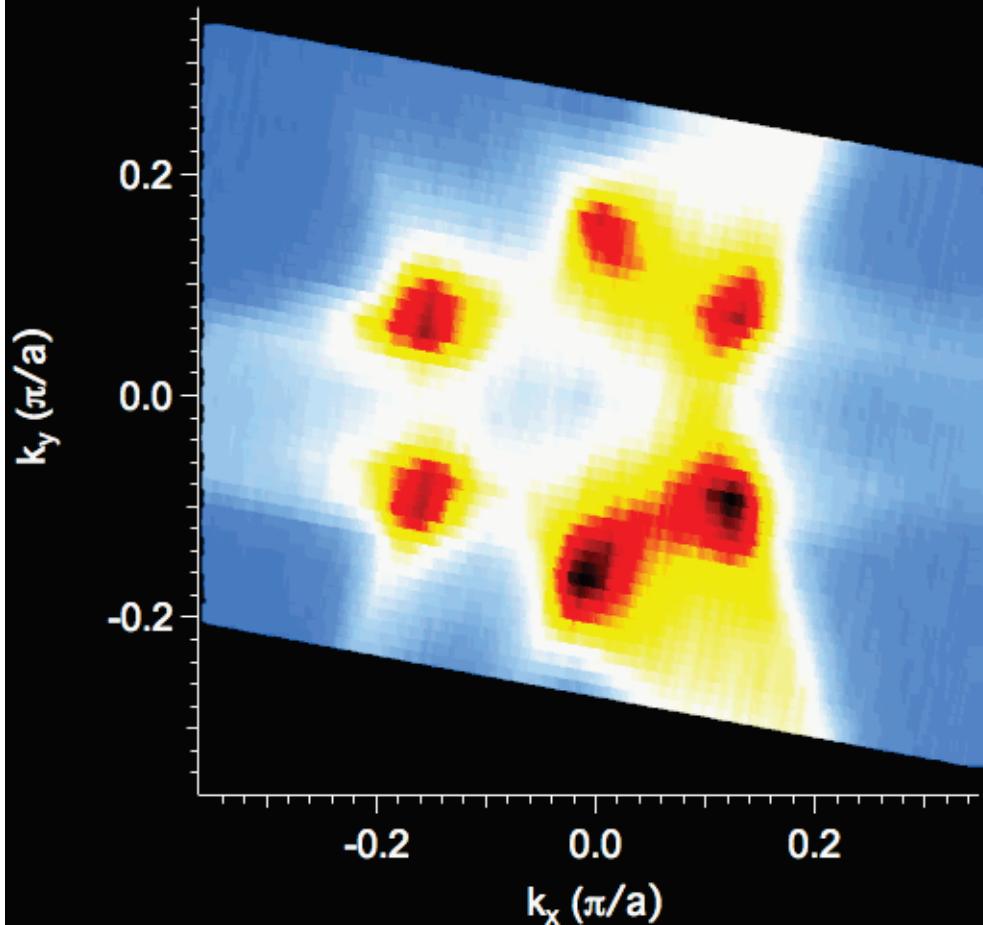
What do these quaternary 3D TI's look like in ARPES ?

One cone per Brillouin zone: Bi₂Te₂Se is a strong TI



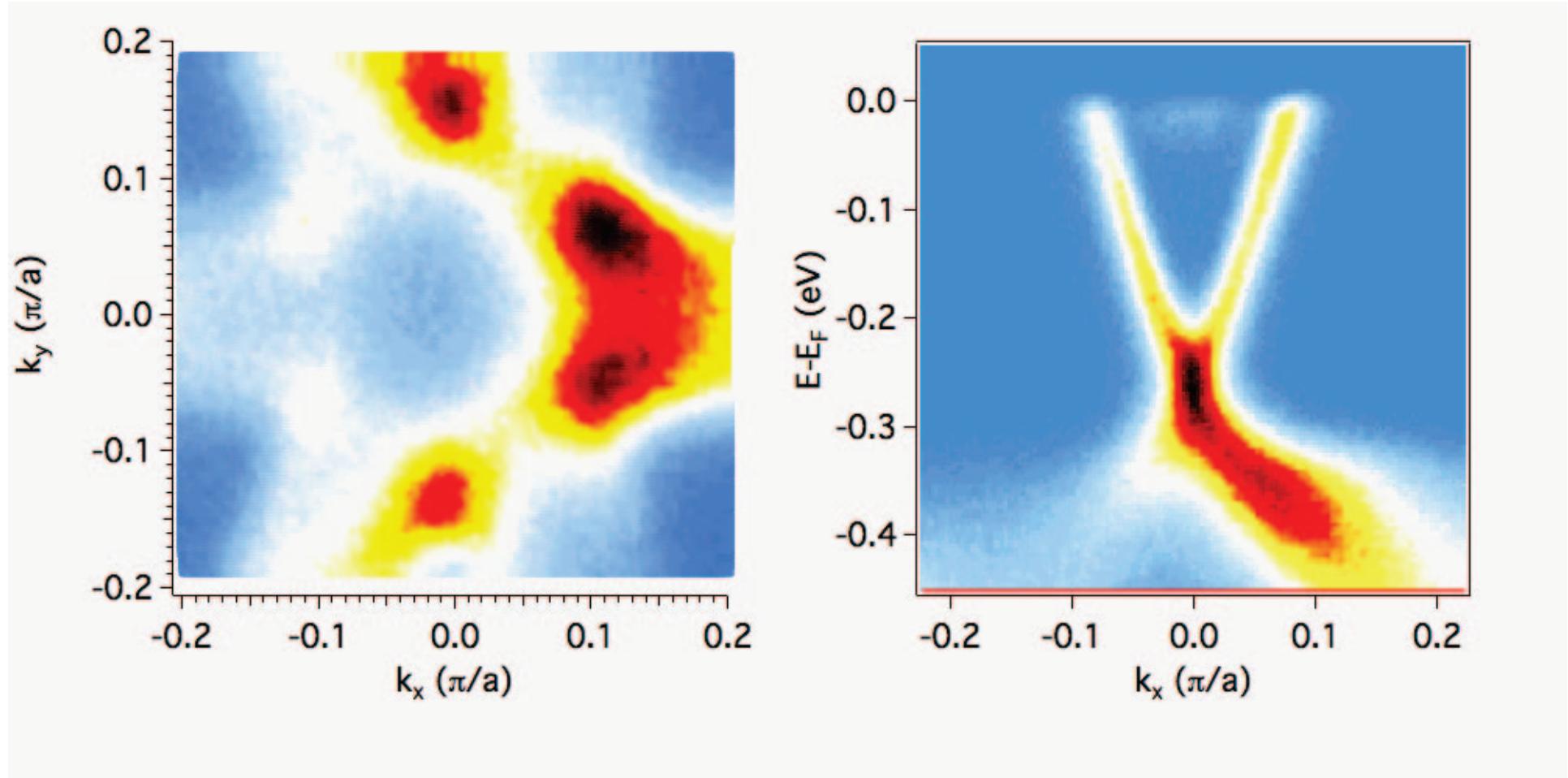
Nick de Jong, MSc thesis: SLS data.

$\text{Bi}_2\text{Te}_2\text{Se}$



data: deJong & vHeumen @Swiss Light Source

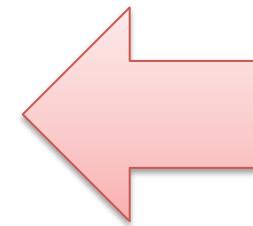
Mapping the cone in $\text{Bi}_{1.5}\text{Sb}_{0.5}\text{Te}_{1.7}\text{Se}_{1.3}$



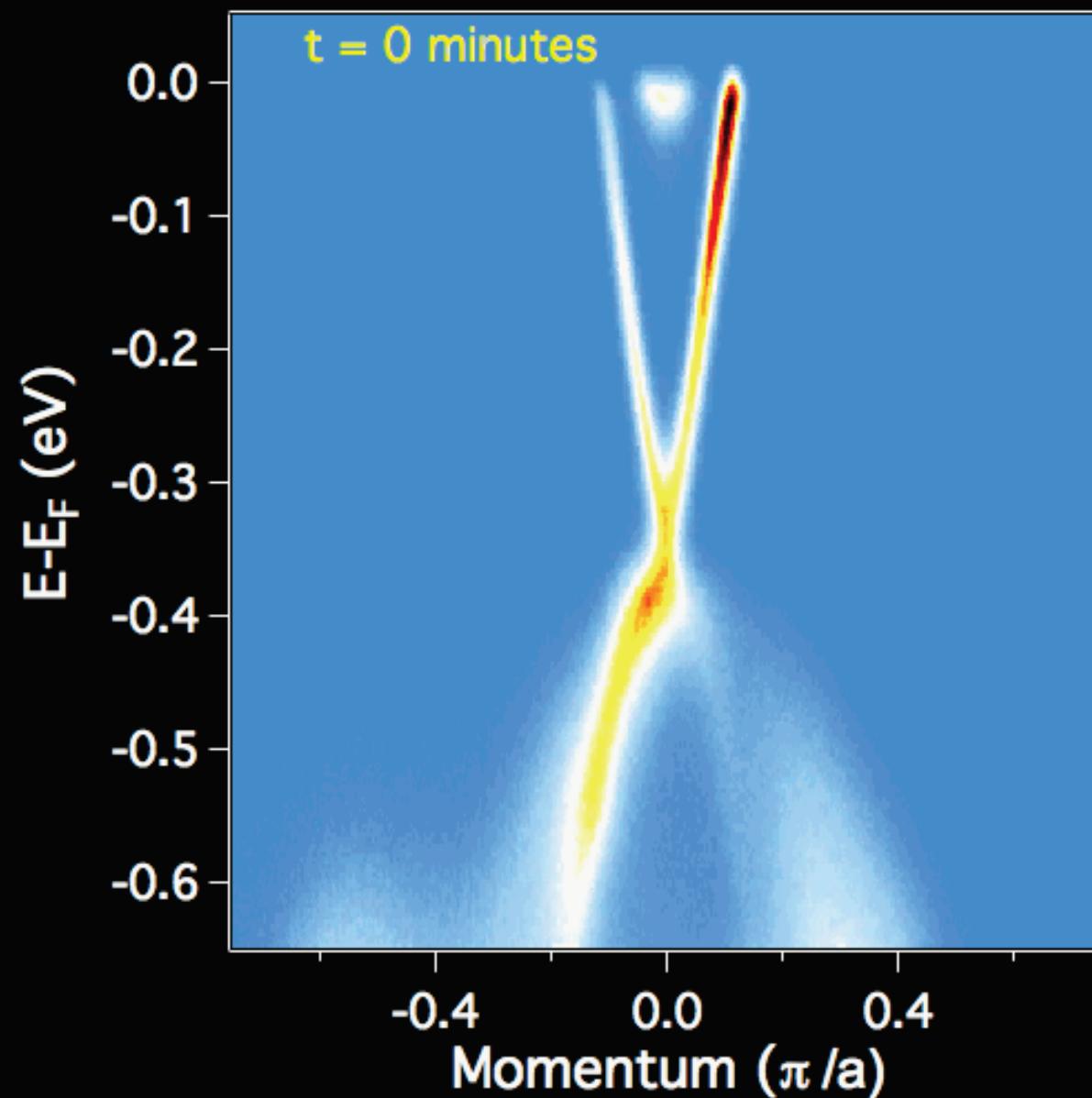
data: v.Heumen @ Swiss Light Source

Overview

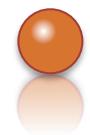
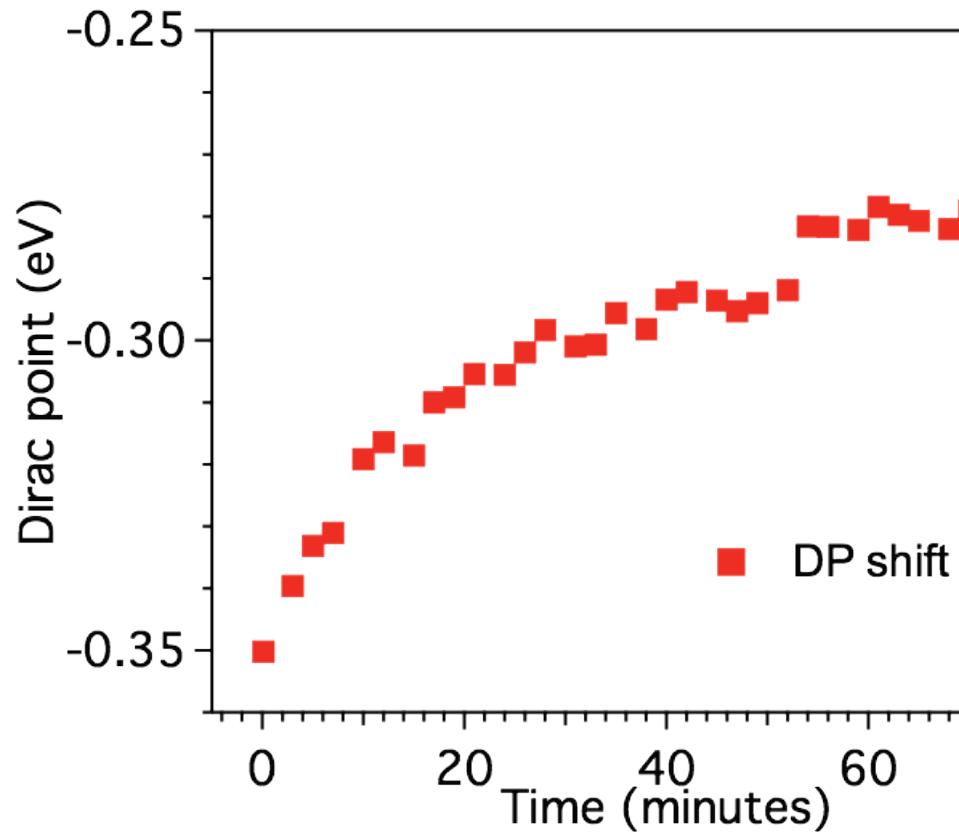
- hitchhiker's guide to TIs
- spectroscopy and microscopy of topological surface states
- towards 3D topological *insulators*
- surprises in the time dependence in ARPES of insulating TI's



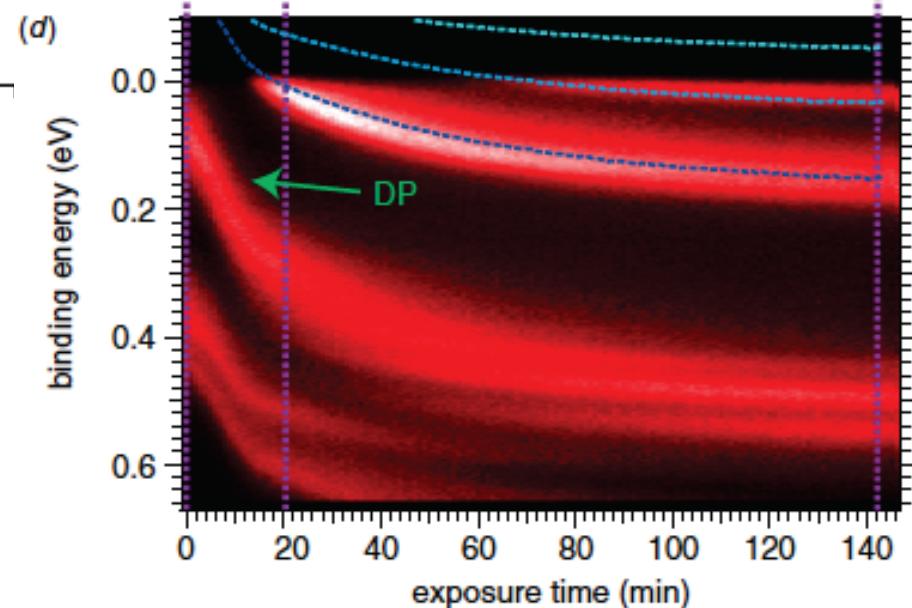
$\text{Bi}_{1.5}\text{Sb}_{0.5}\text{Te}_{1.7}\text{Se}_{1.3}$: as a function of time in the beam



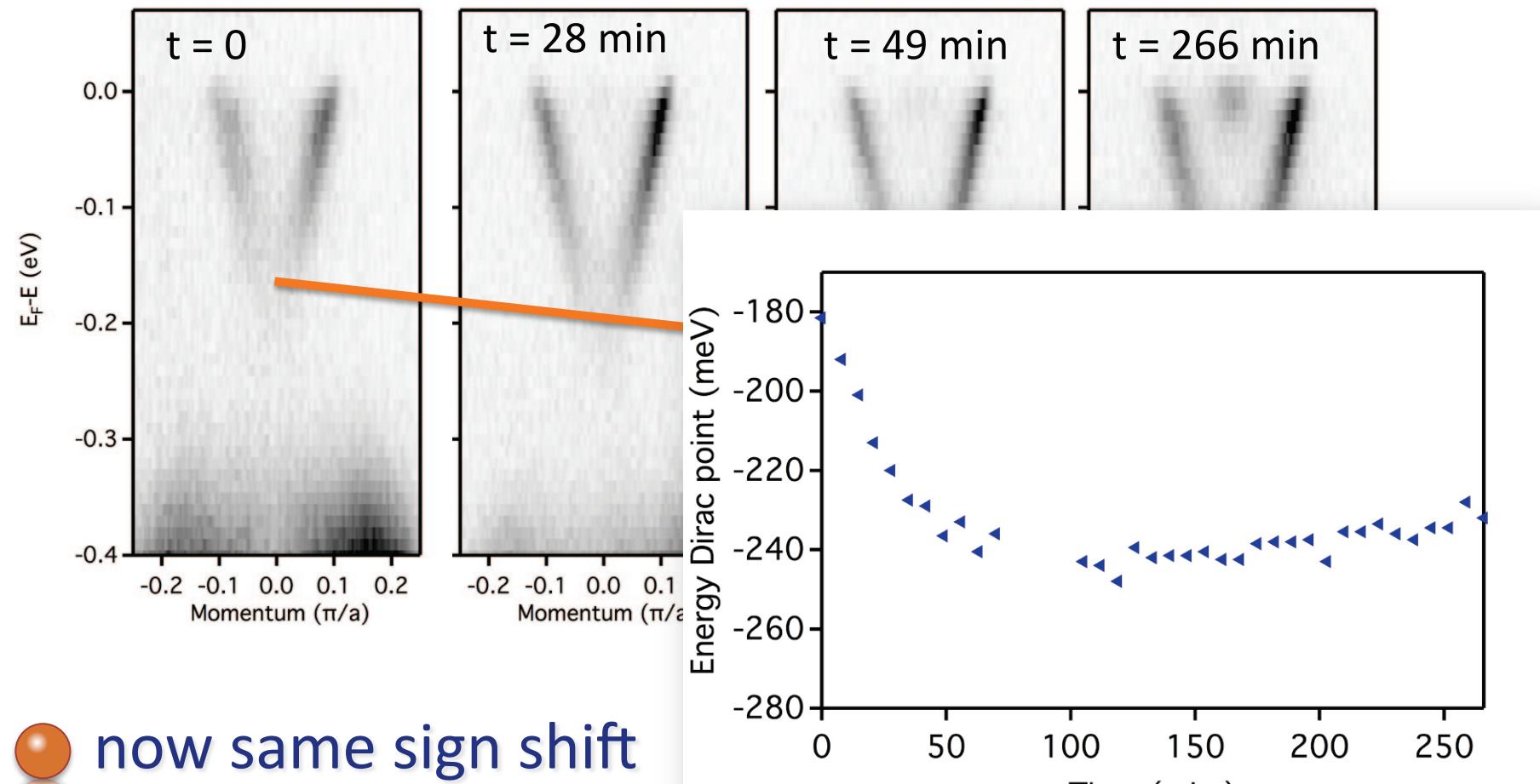
$\text{Bi}_{1.5}\text{Sb}_{0.5}\text{Te}_{1.7}\text{Se}_{1.3}$: as a function of (photon) time



opposite shift to Bi_2Se_3 with time



$\text{Bi}_{1.5}\text{Sb}_{0.5}\text{Te}_{1.7}\text{Se}_{1.3}$: as a function of time – low flux

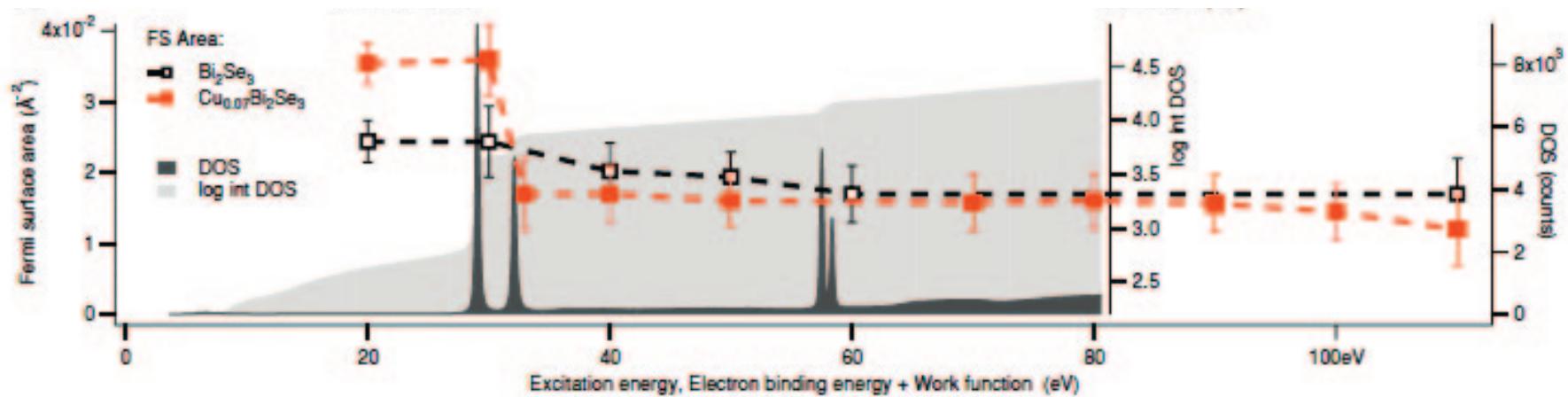


now same sign shift
as Bi_2Se_3 with time....

Flux reduced by factor 65
23 eV @ 16 K

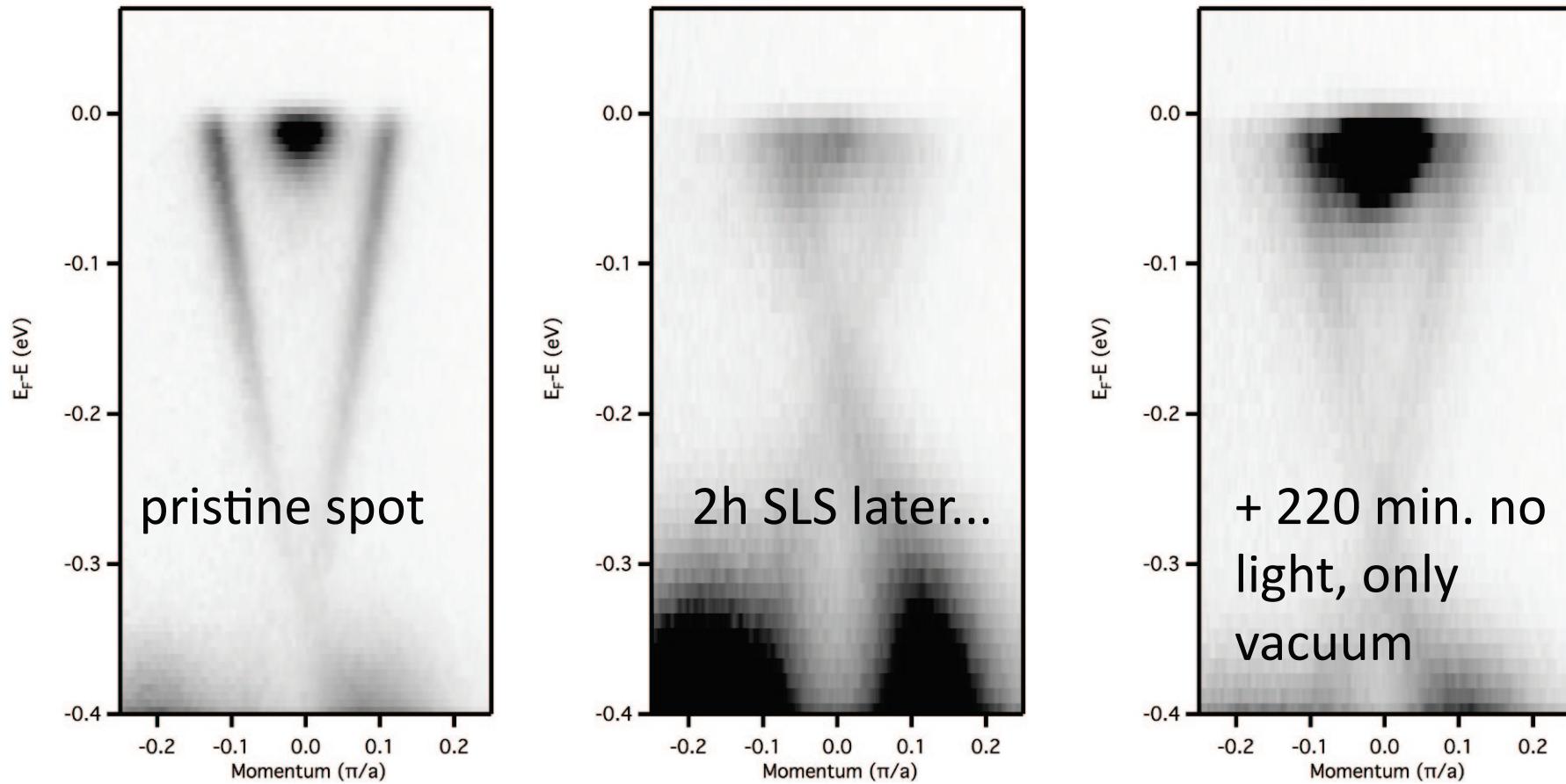
Very clear surface photovoltage

- e-h pairs from (very intense) photon beam reduce band bending at surface
- seen in $\text{Cu}_x\text{Bi}_2\text{Se}_3$ by Kordyuk et al.



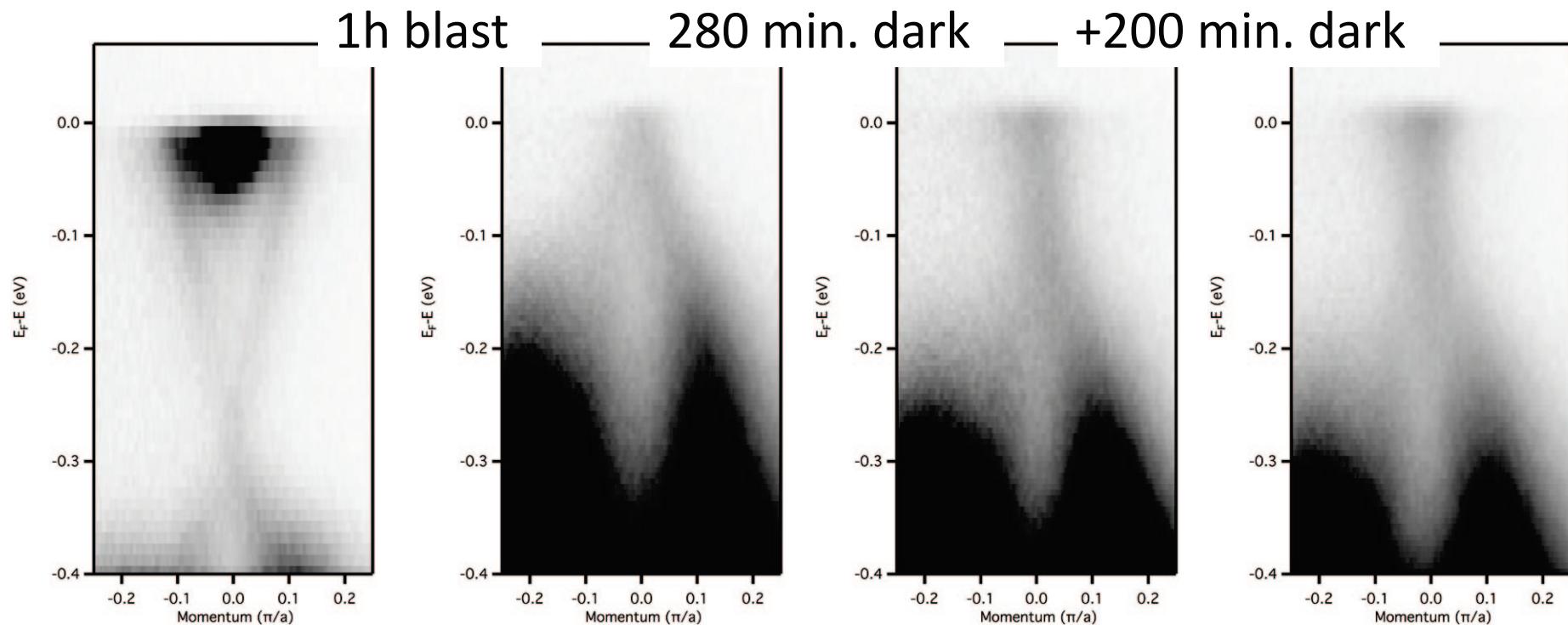
Kordyuk et al., PRB 2011

BSTS: vacuum shifts one way, photons the opposite



BSTS: how far can we go?

.....photon blasting



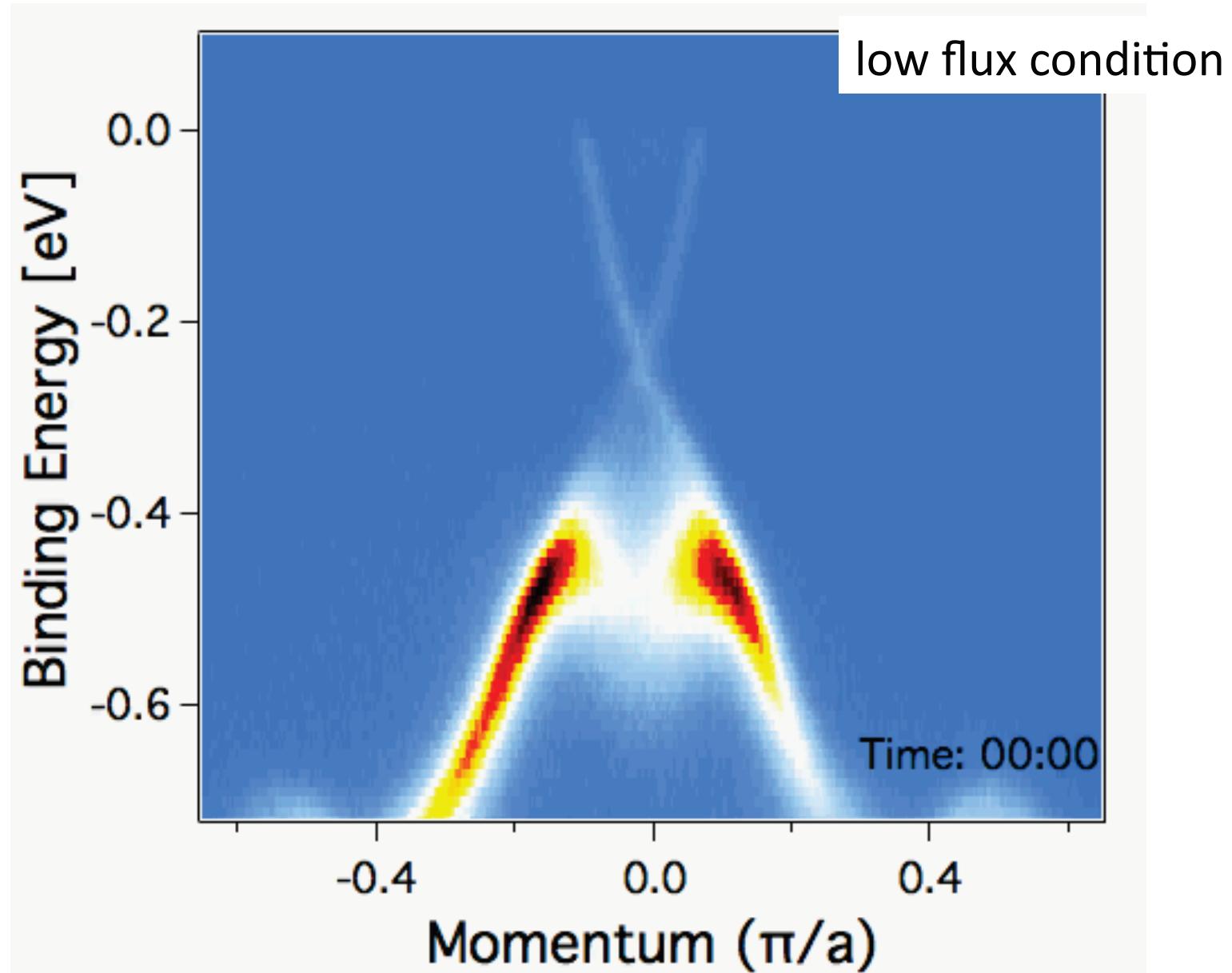
total SPV (upward shift) exceeds 250 meV



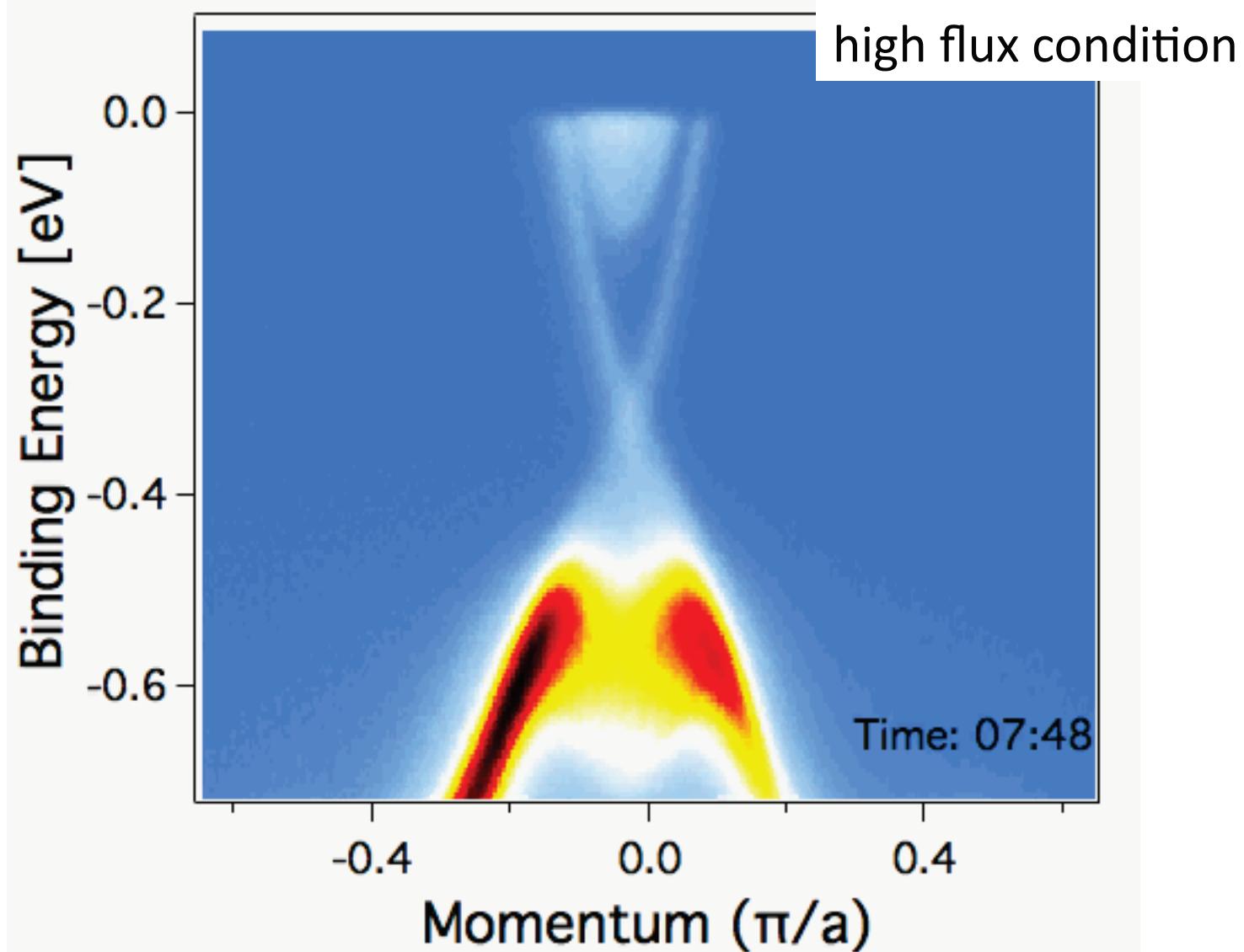
shift back starts once SR is off

Flux increased by factor 8
130 eV @ 16 K

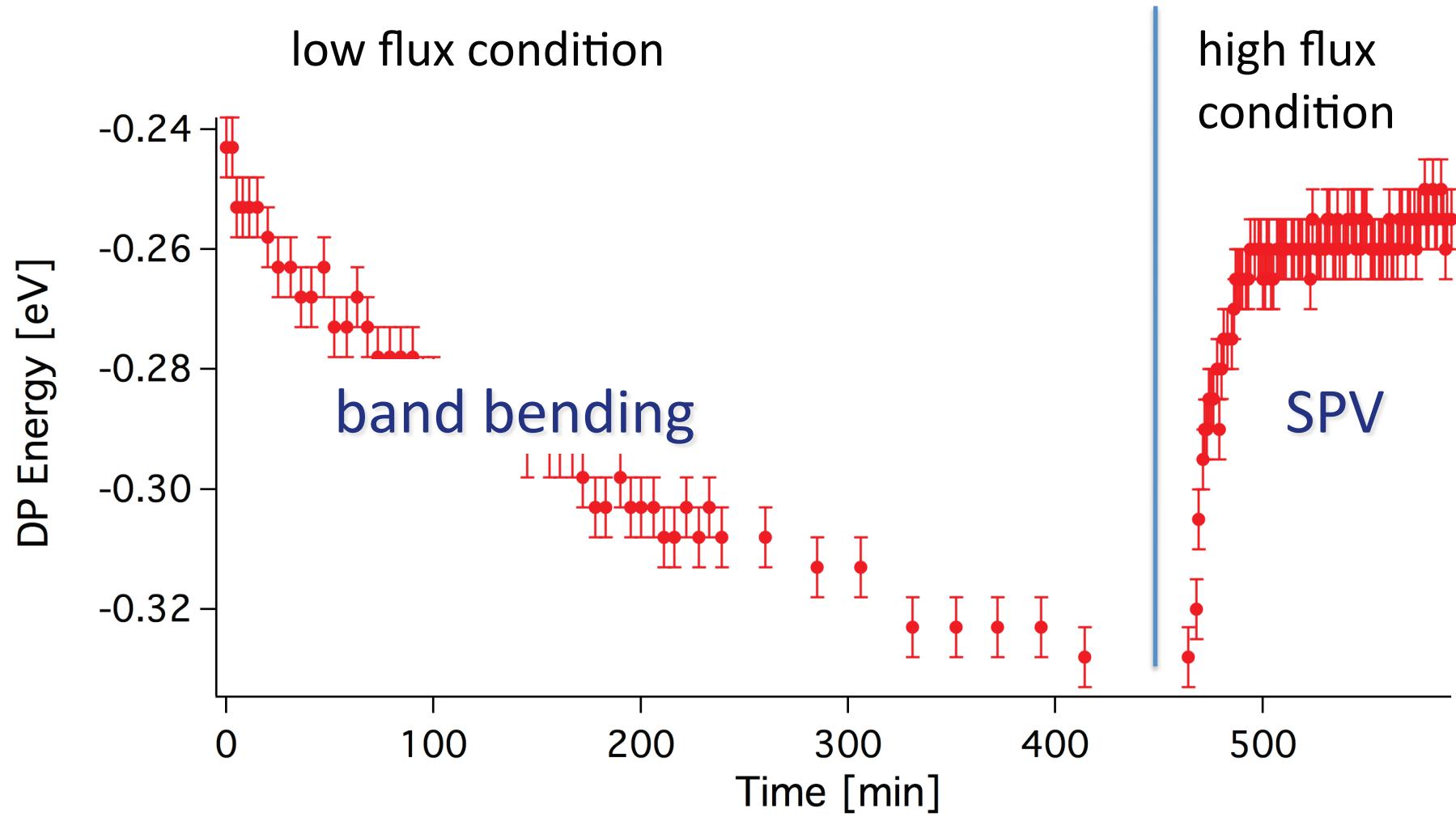
Return to Bi_2Se_3



Return to Bi_2Se_3



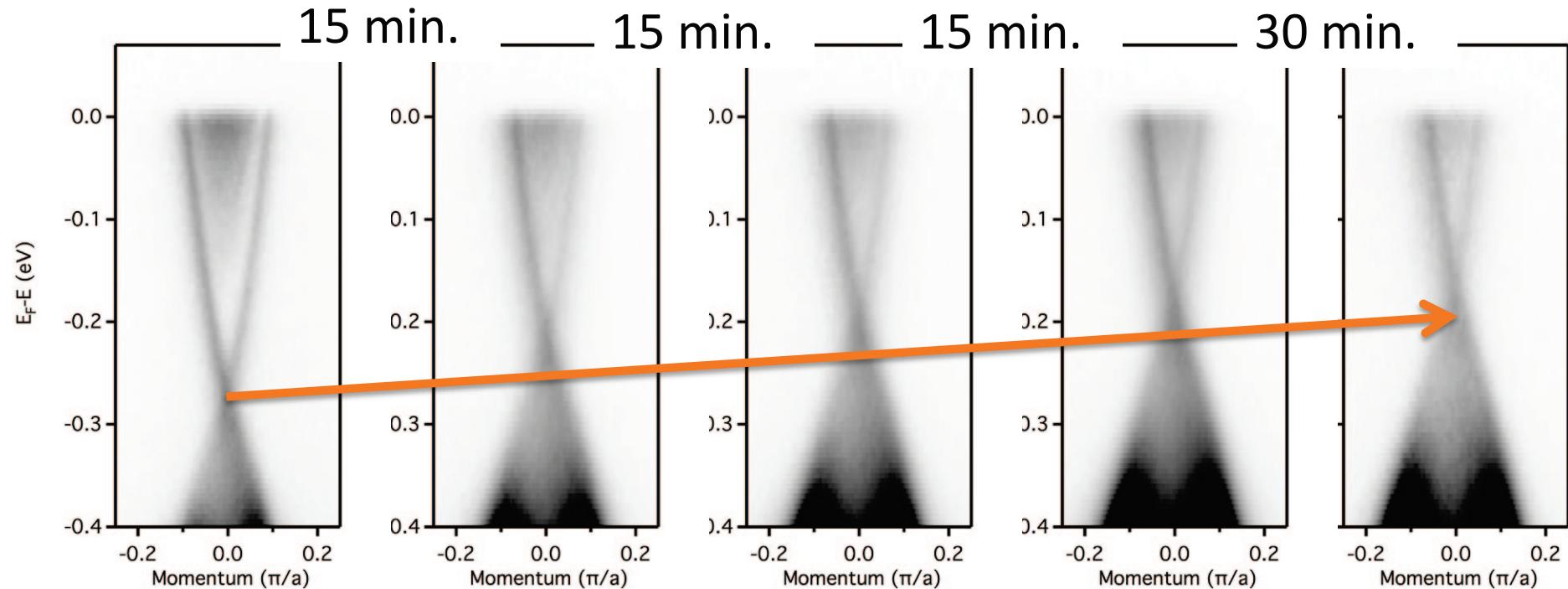
Return to Bi_2Se_3



close to complete flattening of bands

Bi_2Se_3 : how far can we go?

.....photon blasting



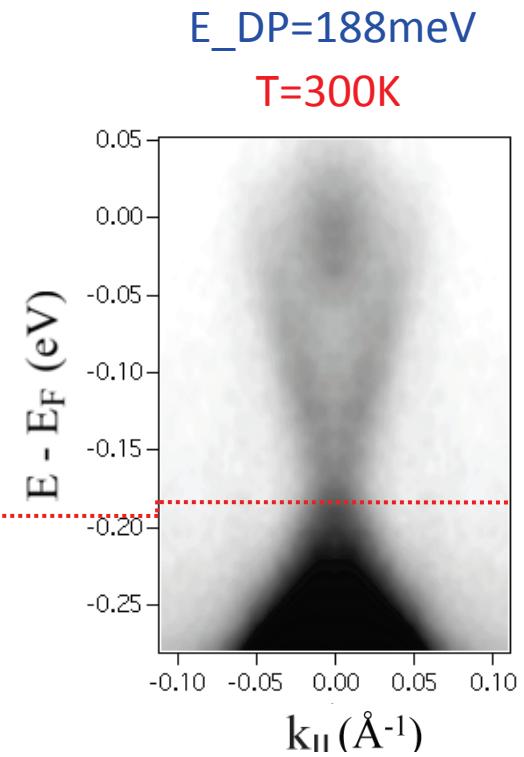
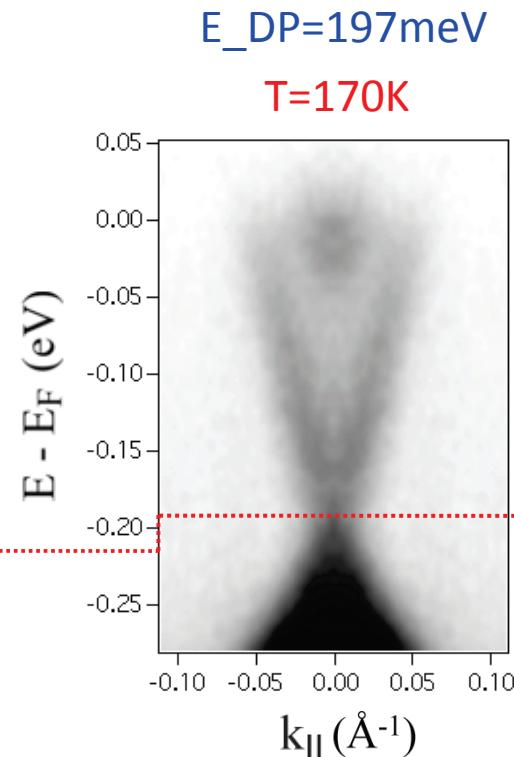
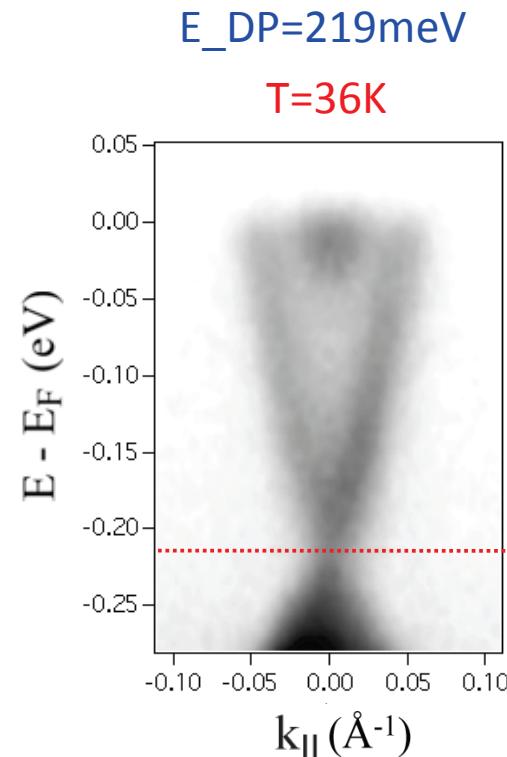
total SPV (upward shift) 170 meV

Frantzeskakis, deJong @SLS

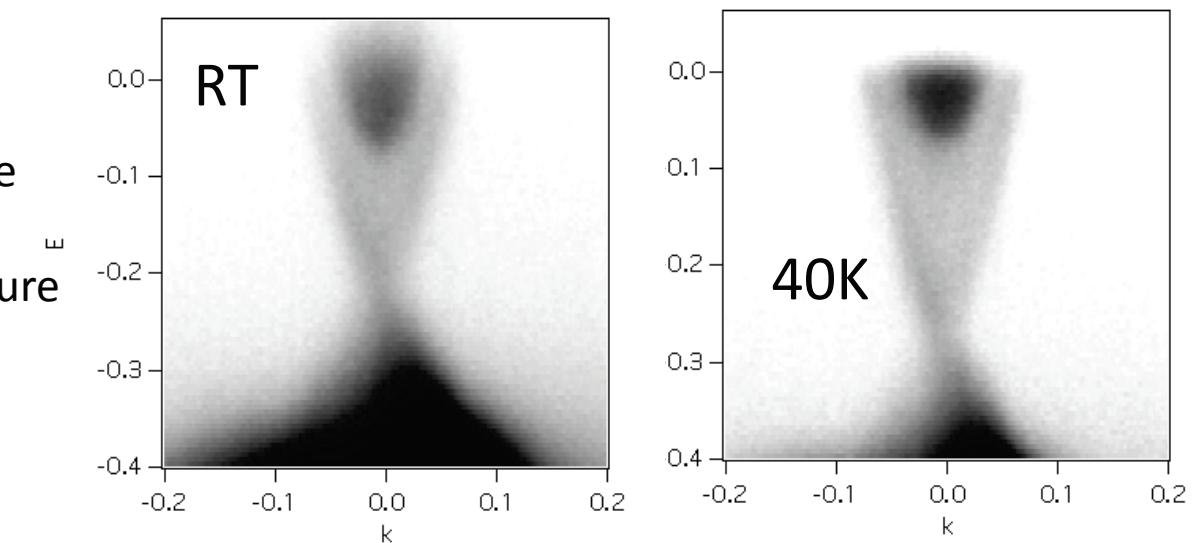
Flux increased by factor 8
130 eV @ 16 K

Temperature dependence: Bi_2Se_3

27eV



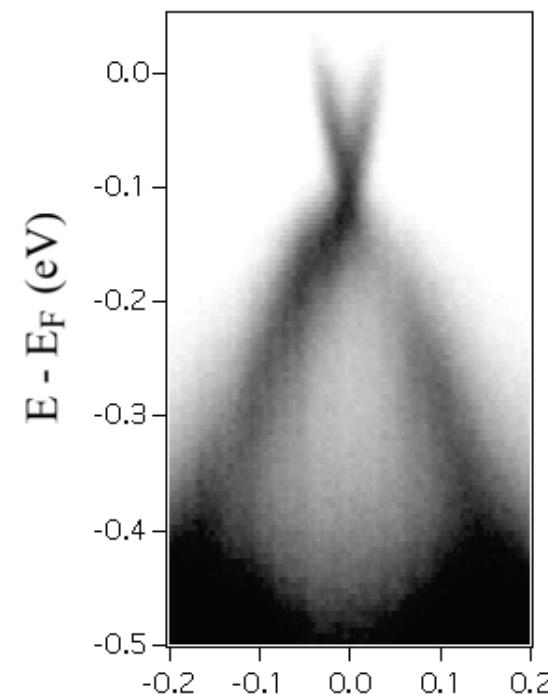
Overnight @RT: measure pristine spot.
The cool (in dark): then re-measure



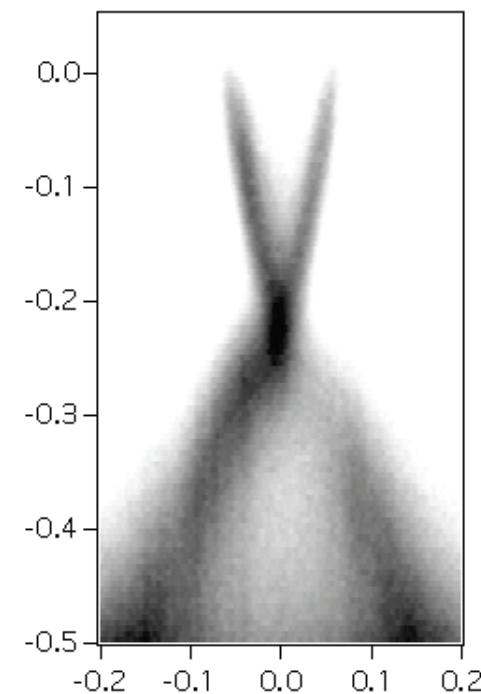
Temperature dependence: BSTS

27eV

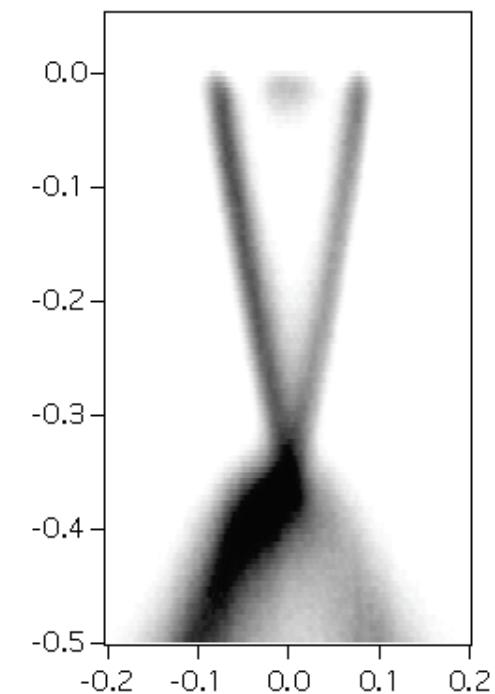
10mins after cleave
RT; not exposed to hν



15h after cleave
RT; not exposed to hν



cooling down to 40K
 Δ_E DP is 125meV



Summary

- good progress → bulk insulating 3D TI's

- clear surface photovoltage:
→ faster when more insulating

none seen for Bi_2Te_3 , also no T-dep of BB

- downward band bending:
→ faster for more insulating
→ stronger at low T

clear correlations between transport properties and ARPES behaviour

Thanks to



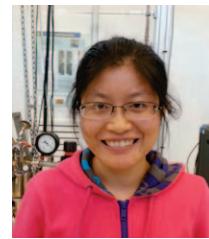
Yingkai
Huang



Dong
Wu



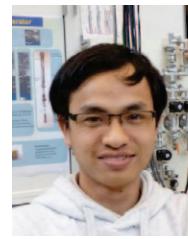
Anne de
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Jiri
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Steve
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